# **NCE Automotive N-Channel Super Trench II Power MOSFET**

#### **Description**

The NCEAP018N85LL uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{\text{DS(ON)}}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

#### **Application**

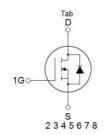
- Automotive application
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

#### **General Features**

- $V_{DS}$  =85V, $I_D$  =330A  $R_{DS(ON)}$ =1.3m $\Omega$  , typical @  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- 100% UIS tested
- 100% ΔVds tested
- Pb-free lead plating
- AEC-Q101 qualified







**Schematic Diagram** 

# **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AP018N85LL	NCEAP018N85LL	TOLL-8L	-	-	-

#### Absolute Maximum Ratings (T<sub>c</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	85	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I <sub>D</sub>	330	А
Drain Current-Continuous(T <sub>C</sub> =100°C)	I <sub>D</sub> (T <sub>C</sub> =100°C)	237	Α
Pulsed Drain Current	I <sub>DM</sub>	1280	Α
Maximum Power Dissipation	P <sub>D</sub>	380	W
Derating factor		2.5	W/°C
Single pulse avalanche energy (Note 1)	E <sub>AS</sub>	2880	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 175	°C

#### **Thermal Characteristic**

Parameter	Symbol	Тур	Max	Unit
Thermal Resistance, Junction-to-Case	Rejc	0.24	0.39	°C/W

# NCEAP018N85LL

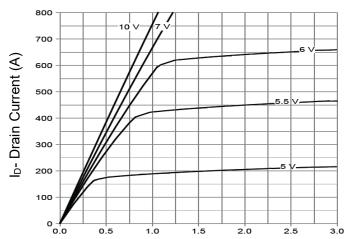
# Electrical Characteristics (T<sub>C</sub>=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	-		<b>-</b>	•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	85	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =85V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	1.3	1.8	mΩ
Gate resistance	R <sub>G</sub>	F=1.0MHz	0.2	3.0	4.0	Ω
Forward Transconductance	<b>G</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =20A	-	200	-	S
Dynamic Characteristics				•		
Input Capacitance	C <sub>lss</sub>	\/ 40\/\\ 0\/	-	14500	18850	pF
Output Capacitance	Coss	$V_{DS}$ =40V, $V_{GS}$ =0V, F=1.0MHz	-	2050	2670	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.UIVIHZ	-	105	210	pF
Switching Characteristics (Note 2)				•		
Turn-on Delay Time	t <sub>d(on)</sub>		-	34	-	nS
Turn-on Rise Time	tr	$V_{DD}$ =40 $V$ , $I_D$ =20 $A$	-	27	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10 $V$ , $R_{G}$ =1.6 $\Omega$	-	78	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	30	-	nS
Total Gate Charge	Qg	\/ 40\/ L 00A	-	240	312	nC
Gate-Source Charge	Qgs	$V_{DS}=40V,I_{D}=20A,$	-	61	79.5	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	72	93.5	nC
Drain-Source Diode Characteristics					· '	
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =20A	-	-	1.2	V
Diode Forward Current	Is		-	-	330	Α
Reverse Recovery Time	t <sub>rr</sub>	$T_J = 25^{\circ}C$ , $I_F = 20A$	-	101	205	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs	-	280	560	nC

#### Notes:

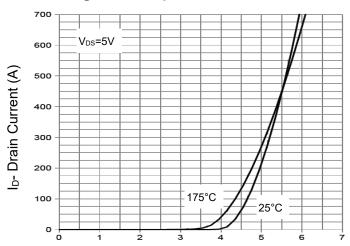
- 1. EAS condition : Tj=25  $^{\circ}\text{C}$  ,VDD=40V,VG=10V,L=0.5mH,Rg=25 $\Omega$
- 2. Guaranteed by design, not subject to production
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of TJ(MAX)=175° C. The SOA curve provides a single pulse rating.

# **Typical Electrical and Thermal Characteristics**



Vds Drain-Source Voltage (V)

## **Figure 1 Output Characteristics**



Vgs Gate-Source Voltage (V)

## **Figure 2 Transfer Characteristics**

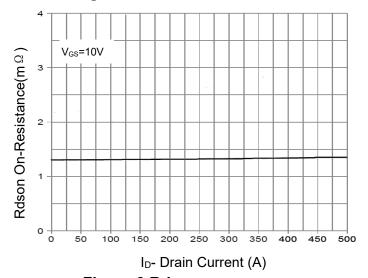
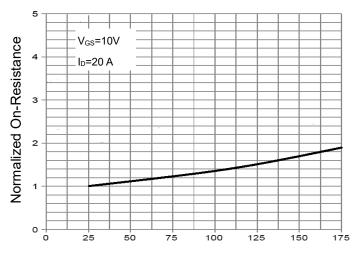


Figure 3 Rdson- Drain Current



T<sub>J</sub>-Junction Temperature(°C)

## Figure 4 Rdson-Junction Temperature

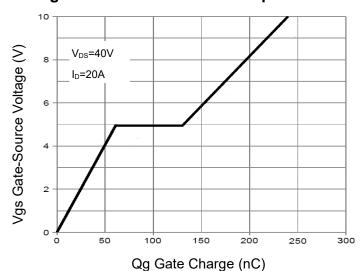
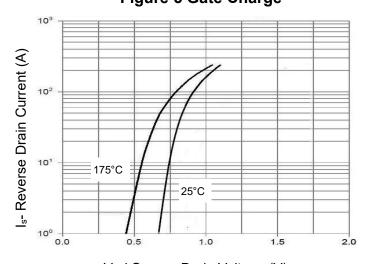


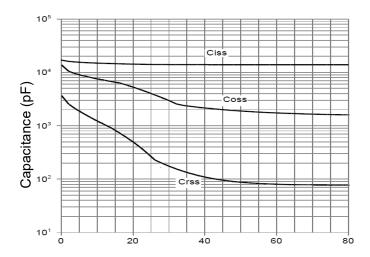
Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)

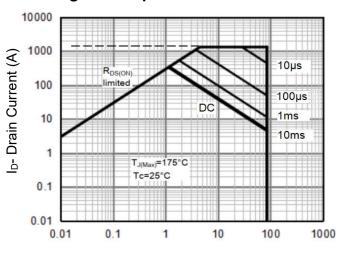
Figure 6 Source- Drain Diode Forward





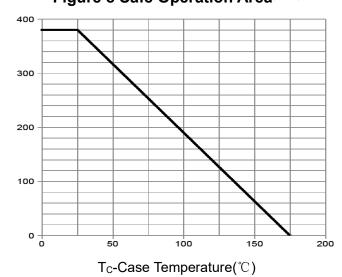
Vds Drain-Source Voltage (V)

Figure 7 Capacitance vs Vds



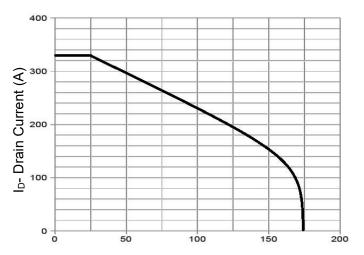
Vds Drain-Source Voltage (V)

Figure 8 Safe Operation Area(Note 3)



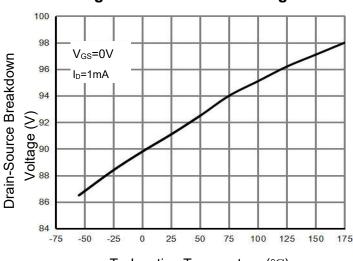
Power Dissipation (W)

Figure 9 Power De-rating



T<sub>C</sub>-Case Temperature (°C)

# Figure 10 Current De-rating



T<sub>J</sub>-Junction Temperature (°C)

## Figure 11 BV<sub>DSS</sub>-Junction Temperature

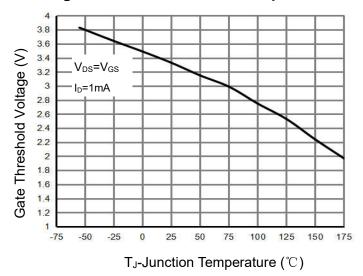
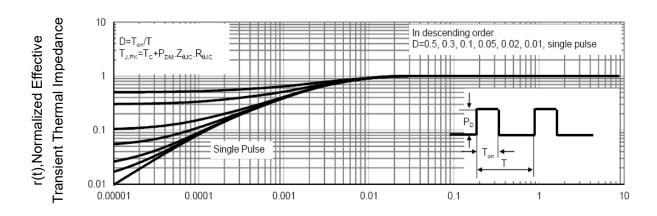


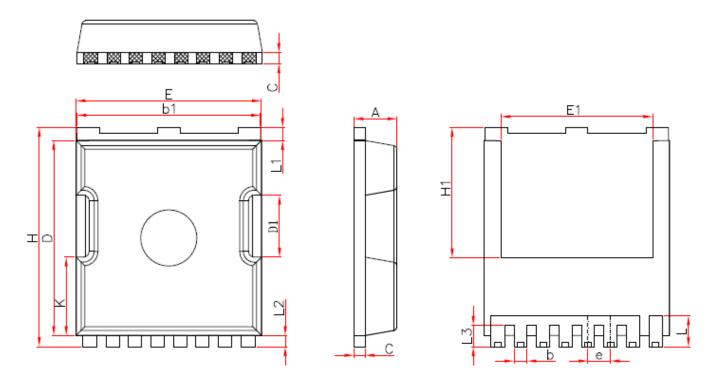
Figure 12 V<sub>GS(th)</sub>-Junction Temperature



Square Wave Pluse Duration(sec)

**Figure 13 Normalized Maximum Transient Thermal Impedance** 

# **TOLL Package Information**



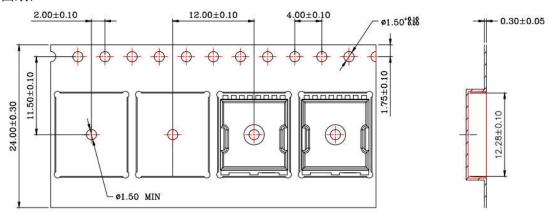
Symbol	Millimeters				
838	Min.	Nom.	Max.		
A	2.20	2.30	2.40		
b	0.65	0.75	0.85		
b1	9.70	9.80	9.90		
C	0.50	0.60	0.70		
D	10.30	10.40	10.50		
D1	3.15	3.3	3.45		
Е	9.70	9.90	10.10		
E1	8.00	8.10	8.20		
е	1.10	1.20	1.30		
Н	11.6	11.7	11.8		
H1	6.85	6.95	7.05		
K	4.08	4.18	4.28		
L	1.60	1.65	2.10		
L1	0.60	0.70	0.80		
L2	0.50	0.60	0.70		
L3	1.05	1.20	1.30		

-10.50±0.10



# Package information

#### 一、载带图纸:



#### Notes:

- 1. All dimensions are in mm.
- 2. Material: Black Conductive Polystyrene Alloy
- 3. 10 sprocket hole pitch cumulative tolerance  $\pm 0.20$ mm.
- 4. Carrier camber is within 1 mm in 250 mm.
- 5. Packing length per 19" reel: 196.0 Meters.
- 6. There must not be foreign body adhesion and the state of the surface must be excellent.
- 7.Surface Resistance 1X10E5~1x10E11 OHMS/SQ

#### 二、包装信息表 (满箱信息)

封装形式	包装方式	盘尺寸	只/盘	盘/内盒	只/内盒	内盒/箱	只/箱
TOLL	编带	13寸	2000	1	2000	8	16000

Wuxi NCE Power Co., Ltd Page 7 V2.0

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# NCEAP018N85LL

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